Customer No.: 31561
Application No.: 10/711,512
Docket No.: 13622-US-PA

REMARKS

Present Status of the Application

The Examiner's indication allowance of claims 1-10, and claims 12-15 would be allowed if rewritten into independent form including all of the limitations of the base claim and any intervening claims is noted with great appreciation.

Claims 1-15 remain pending in the present application. For at least the following reasons, Applicants respectfully submit that claim 11 patently define over prior art of record and reconsideration of this application is respectfully requested.

Discussion of the claim rejection under 35 USC 102

The Office Action rejected Claim 11 under 35 U.S.C. 102(e) as being anticipated by Olgado et al. (US-6,770,565, hereinafter Olgado).

Applicants respectfully disagree and respectfully submit that Olgado cannot anticipate the proposed independent claim 11 because Olgado substantially fails to teach or disclose each and every elements of the claimed invention as claimed in the proposed independent claim 11. More specifically, Olgado substantially fails to teach or disclose a method for improving uniformity of thickness of a thin film, adapted for a chemical vapor deposition process, comprising: ***[forming the thin film with uniform thickness by rotating a wafer with an angle while depositing the thin film on the wafer]*** as required by the proposed independent claim 11. The advantage of the features recited above is that at least the thin film may be deposited with a substantially uniform thickness.

Instead, Olgado, at FIG. 8, col. 10, lines 40-47, and the whole disclosure,

substantially discloses a Chemical Mechanical Process (CMP) for PLANARIZING a metal conductive layer 906 formed over the substrate 900 comprising rotating the substrate 900 (at a rotation speed of at least about 150 rpm) and delivering the etching solution on the top surface of the substrate. Accordingly, it is clear that the claimed invention as claimed in the proposed claim 11, which is directed to a process of depositing a thin film on the wafer is totally different from the CMP process taught by Ogaldo in which a top portion of metal conductive layer 906 formed on the substrate 900 is removed. Thus, Olgado cannot possibly anticipate the proposed independent claim 11 in this regard.

Therefore, it is clear that Ogaldo substantially fails to teach or disclose a method for improving uniformity of thickness of a thin film, adapted for a chemical vapor deposition process, comprising: ***[forming the thin film with uniform thickness by rotating a wafer with an angle while depositing the thin film on the wafer]*** as required by the proposed independent claim 11, instead Olgaldo substantially teaches a CMP process for planarizing the metal conductive layer 906 formed on the substrate 900. Therefore, Olgado fails to teach or disclose each and every features of claim 11 and therefore Olgado cannot possibly anticipate the proposed independent claim 11 in this regard.

For at least the foregoing reasons, Applicants respectfully submit that claim 11 patently define over Ogaldo. Reconsideration and withdrawal of above rejections is respectfully requested.

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CONCLUSION

For at least the foregoing reasons, it is believed that all the pending claims 1-15 of the present application patently define over the prior art and are in proper condition for allowance. If the Examiner believes that a telephone conference would expedite the examination of the above-identified patent application, the Examiner is invited to call the undersigned.

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Respectfully submitted,

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